



STPS10150CT/CG

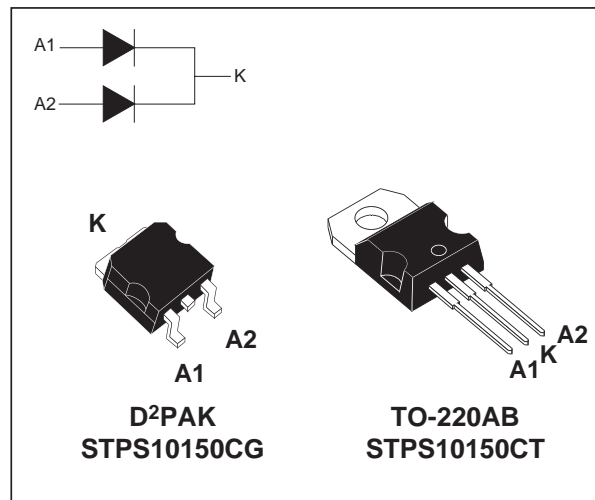
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 5 A
V_{RRM}	150 V
T_j	175°C
$V_F (max)$	0.75 V

FEATURES AND BENEFITS

- HIGH JUNCTION TEMPERATURE CAPABILITY
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW LEAKAGE CURRENT



DESCRIPTION

Dual center tap schottky rectifier designed for high frequency Switched Mode Power Supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
V_{RRM}	Repetitive peak reverse voltage			150	V	
$I_{F(RMS)}$	RMS forward current			10	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB	$T_c = 155^\circ\text{C}$	per diode	5	A
		D ² PAK		per device	10	
I_{FSM}	Surge non repetitive forward current		tp = 10 ms sinusoidal	120	A	
T_{stg}	Storage temperature range			- 65 to + 175	°C	
T_j	Maximum operating junction temperature			175	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μ s	

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THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
R _{th(j-c)}	Junction to case	TO-220AB / D ² PAK	Per diode	4	°C/W
		TO-220AB / D ² PAK	Total	2.4	
R _{th(c)}		TO-220AB / D ² PAK	Coupling	0.7	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			2.0	μA
		T _j = 125°C			0.40	2.0	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 5 A			0.92	V
		T _j = 125°C	I _F = 5 A		0.69	0.75	
		T _j = 25°C	I _F = 10 A			1	
		T _j = 125°C	I _F = 10 A		0.79	0.85	

Pulse test : * tp = 5 ms, δ < 2%
 ** tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.65 I_{F(AV)} + 0.02 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

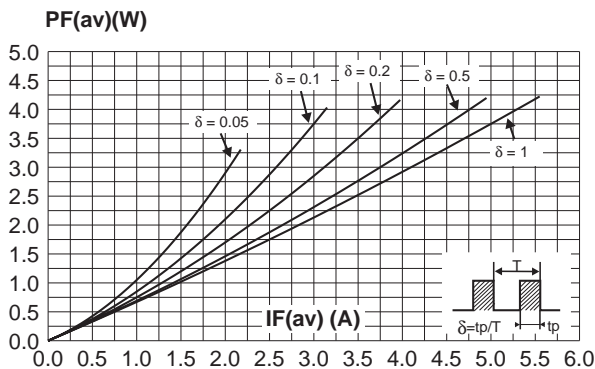


Fig. 2: Average forward current versus ambient temperature (δ = 0.5, per diode).

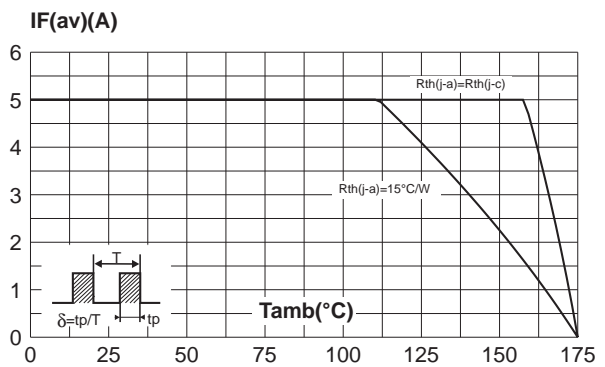


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

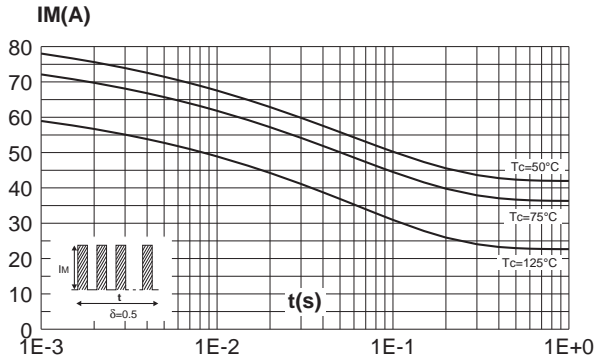


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration (per diode).

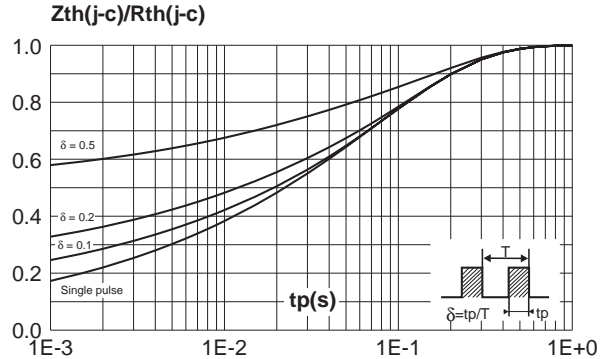


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode)

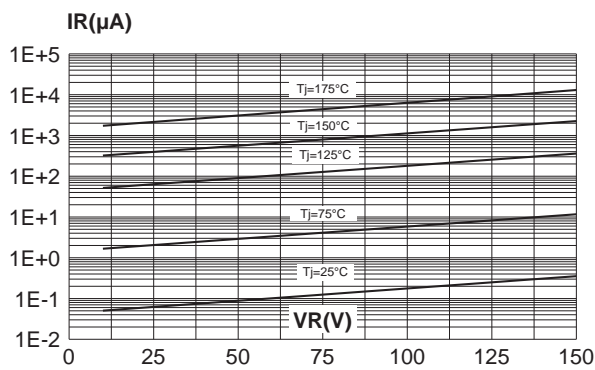


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

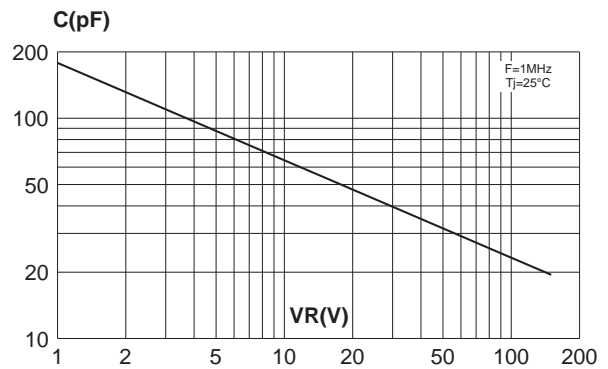


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

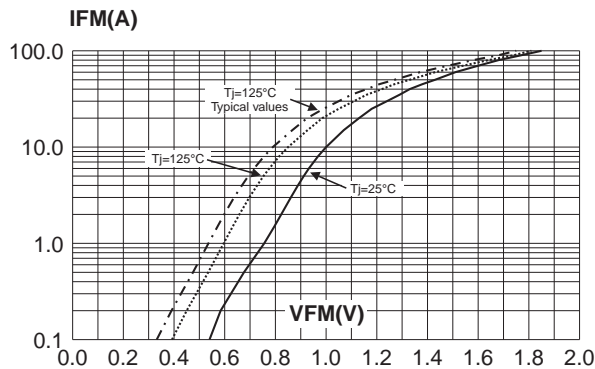
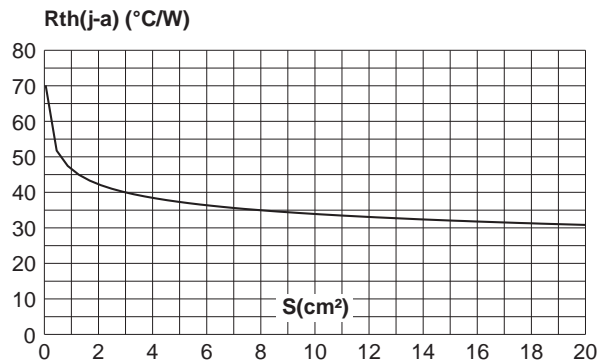
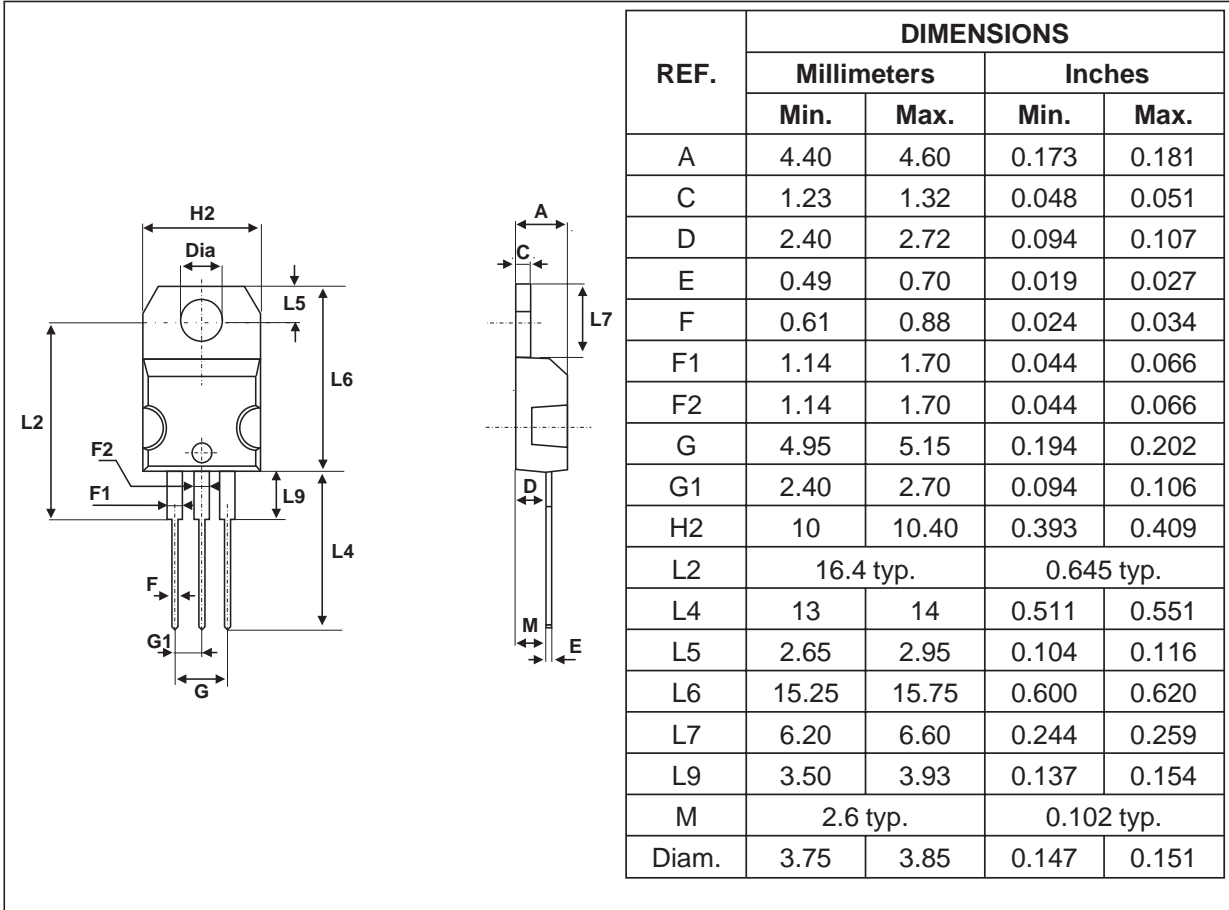


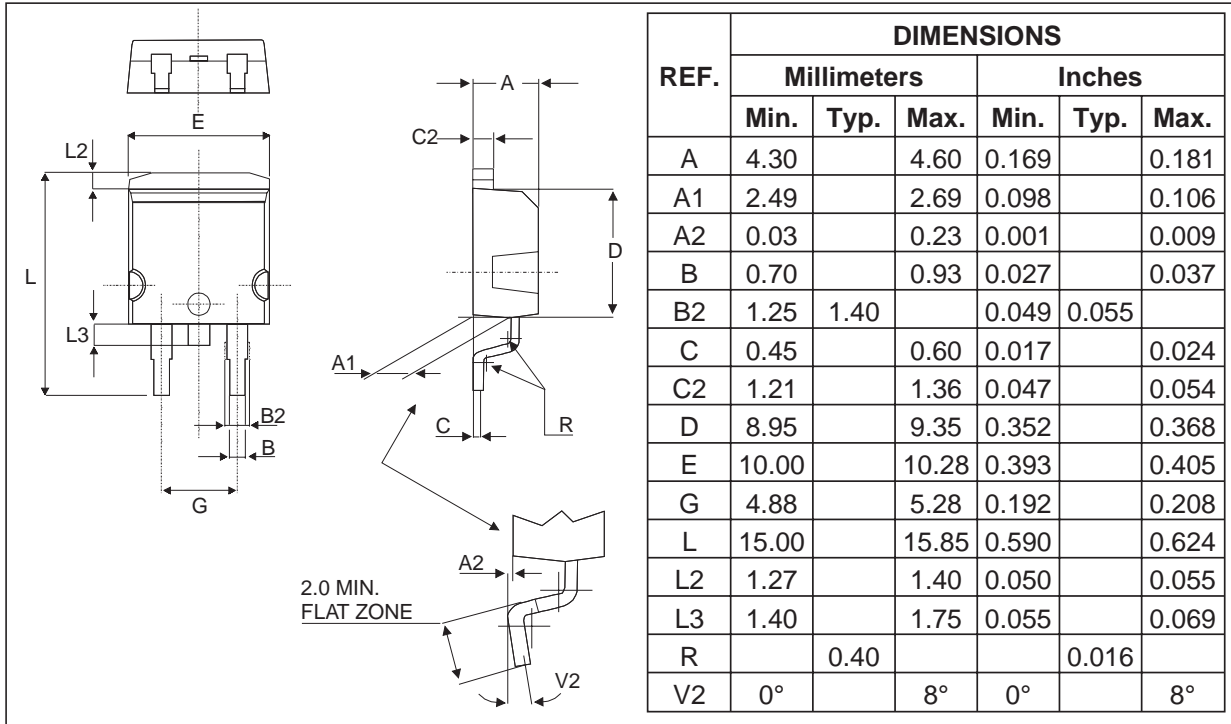
Fig. 8: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: 35µm) (STPS10150CG only).



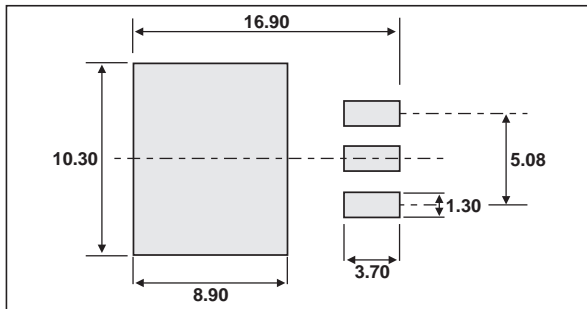
PACKAGE MECHANICAL DATA
TO-220AB



PACKAGE MECHANICAL DATA
D²PAK



FOOT PRINT DIMENSIONS (in millimeters)



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